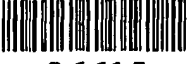
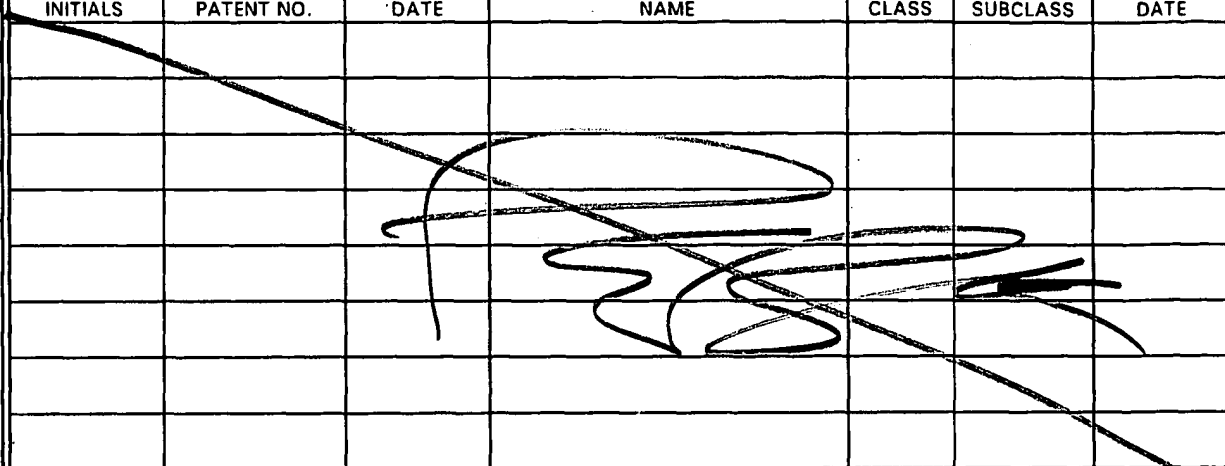
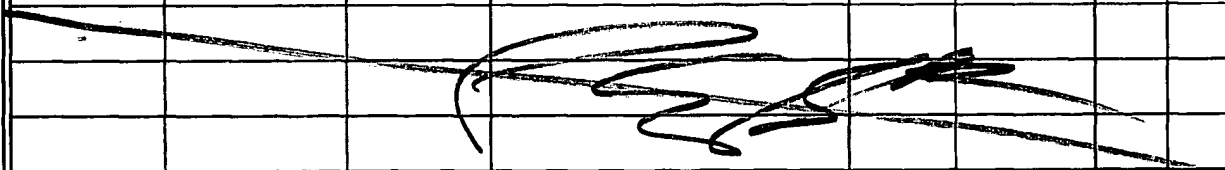


<b>INFORMATION DISCLOSURE CITATION</b> PTO-1449		 <b>26615</b> <small>PATENT TRADEMARK OFFICE</small>		ATTORNEY'S DKT No. H1132		APPLICATION No. Unassigned	
				APPLICANT(S) Ming-Ren Lin et al.		10/6/14 051	
				FILING DATE July 8, 2003		GROUP Unassigned 2815	

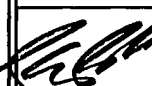




  

U.S. PATENT DOCUMENTS								
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE		
								



  

FOREIGN PATENT DOCUMENTS								
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation		
						Yes	No	
								

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	
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EXAMINER 	DATE CONSIDERED 
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